

INCHANGE SEMICONDUCTOR

Isc N-Channel MOSFET Transistor

NTPF082N65S3F

FEATURES

- With TO-220F package
- · Low input capacitance and gate charge
- · Low gate input resistance
- Reduced switching and conduction losses
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

Switching applications

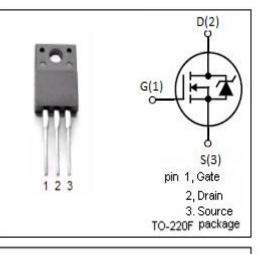
| ABSOLUTE MAXIMUM RATINGS(Ta=25 C) | | | | | | |
|-----------------------------------|---|------------|------|--|--|--|
| SYMBOL | PARAMETER | VALUE | UNIT | | | |
| V _{DSS} | Drain-Source Voltage | 650 | V | | | |
| V _{GSS} | Gate-Source Voltage | ±30 | V | | | |
| ID | Drain Current-Continuous @Tc=25℃ (V _{GS} at 10V) Tc=100℃ | 40 25.5 | A | | | |
| I _{DM} | Drain Current-Single Pulsed | 100 | A | | | |
| PD | Total Dissipation @Tc=25°C | 50 | W | | | |
| Tj | Max. Operating Junction Temperature | 150 | °C | | | |
| T _{stg} | Storage Temperature | -55~150 | °C | | | |

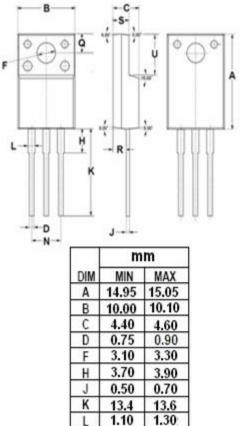
ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

• THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | | UNIT | |
|-----------|--|------|--------------|--|
| Rth(ch-c) | Channel-to-case thermal resistance | 2.62 | °C /W | |
| Rth(ch-a) | th(ch-a) Channel-to-ambient thermal resistance | | °C/W | |

1





5.00

2.70

2.20

6.40

Ν

Q

R

5

5.20

2.90

2.40

2.90

6.60

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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | ТҮР | MAX | UNIT |
|----------------------|--------------------------------|--|-----|-----|-----------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; I _D =1mA | 650 | | | V |
| V _{GS} (th) | Gate Threshold Voltage | V _{DS} = V _{GS} ; I _D =4mA | 3.0 | | 5.0 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D =20A | | 70 | 82 | mΩ |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} = ±30V;V _{DS} =0V | | | ±0.1 | μA |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} = 650V; V _{GS} = 0V;Tj=25℃ V _{DS} = 520V; V _{GS} = 0V; Tj=125℃ | | | 10 100 | μA |
| V _{SDF} | Diode forward voltage | I_{SD} =20A, V_{GS} = 0 V | | | 1.3 | v |

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